

IN THE CLAIMS:

Please AMEND claim 28 as follows:

28. (Twice Amended) A semiconductor device, comprising:
- a substrate;
 - a gate electrode provided on said substrate;
 - a diffusion region formed in said substrate adjacent to said gate electrode;
 - a side-wall insulation film formed on a side wall of said gate electrode;
 - a self-aligned contact hole defined by said side-wall oxide film and exposing said diffusion region; and
 - a silicide region formed selectively on a surface of said diffusion region;
- wherein said semiconductor device further includes;
- a first insulation film provided on said gate electrode so as to cover said side wall oxide film partially;
 - a second insulation film having a composition different from a composition of said first insulation film and provided on said first insulation film;
 - an interlayer insulation film deposited on said second insulation film;
 - a contact hole formed in said interlayer insulation film, said contact hole extending through said first and second insulation films and exposing said self-aligned contact hole;
 - said first insulation film contains H₂O with an amount smaller than about 2.4 wt%.